



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

DUAL/QUAD DSPLL ANY-FREQUENCY, ANY-OUTPUT JITTER ATTENUATORS

Features

- Four or two independent DSPLLs in a single monolithic IC
- Each DSPLL generates any output frequency from any input frequency
- Input frequency range:
 - Differential: 8 kHz to 750 MHz
 - LVCMS: 8 kHz to 250 MHz
- Output frequency range:
 - Differential: up to 712.5 MHz
 - LVCMS: up to 250 MHz
- Ultra low jitter: <100 fs typ (12 kHz–20 MHz)
- Flexible crosspoints route any input to any output clock
- Programmable jitter attenuation bandwidth per DSPLL: 0.1 Hz to 4 kHz programming range
- Highly configurable outputs compatible with LVDS, LVPECL, LVCMS, CML, and HCSL with programmable signal amplitude
- Status monitoring (LOS, OOF, LOL)
- Hitless input clock switching: automatic or manual
- Locks to gapped clock inputs
- Automatic free-run and holdover modes
- Fastlock feature for low nominal bandwidths
- Glitchless on-the-fly DSPLL frequency changes
- DCO mode: as low as 0.01 ppb steps per DSPLL
- Core voltage:
 - V_{DD} : 1.8 V $\pm 5\%$
 - V_{DDA} : 3.3 V $\pm 5\%$
- Independent output clock supply pins: 3.3, 2.5, or 1.8 V
- Output-output skew: <20 ps (typ) per DSPLL
- Serial interface: I²C or SPI
- In-circuit programmable with non-volatile OTP memory
- ClockBuilderTM Pro software tool simplifies device configuration
- Si5347: Quad DSPLL, 4 input, 4 or 8 output, 64 QFN
- Si5346: Dual DSPLL, 4 input, 4 output, 44 QFN
- Temperature range: -40 to +85 °C
- Pb-free, RoHS-6 compliant

Device Selector Guide

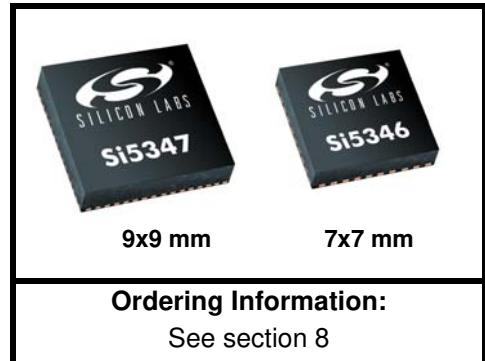
Grade	PLLs/OUTs	Max Output Freq	Frequency Synthesis Modes
Si5347A	4/8	712.5 MHz	Integer + Fractional
Si5347C	4/4	712.5 MHz	Integer + Fractional
Si5346A	2/4	712.5 MHz	Integer + Fractional
Si5347B	4/8	350 MHz	Integer + Fractional
Si5347D	4/4	350 MHz	Integer + Fractional
Si5346B	2/4	350 MHz	Integer + Fractional

Applications

- OTN Muxponders and Transponders
- Carrier Ethernet switches
- 10/40/100G network line cards
- Broadcast video
- 10GbE/10 GbE/100 GbE Synchronous Ethernet (ITU-T G.8262)

Description

The Si5347 is a high performance jitter attenuating clock multiplier which integrates four any-frequency DSPLLs for applications that require maximum integration and independent timing paths. The Si5346 is a dual DSPLL version in a smaller package. Each DSPLL has access to any of the four inputs and can provide low jitter clocks on any of the device outputs. Based on 4th generation DSPLL technology, these devices provide any-frequency conversion with typical jitter performance under 100 fs. Each DSPLL supports independent free-run, holdover modes of operation, as well as automatic and hitless input clock switching. The Si5347/46 is programmable via a serial interface with in-circuit programmable non-volatile memory so that it always powers up in a known configuration. Programming the Si5347/46 is easy with Silicon Labs' [ClockBuilder Pro](#) software. Factory pre-programmed devices are also available.



Ordering Information:

See section 8

Functional Block Diagram

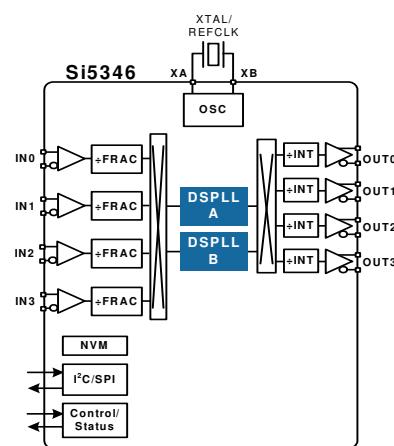
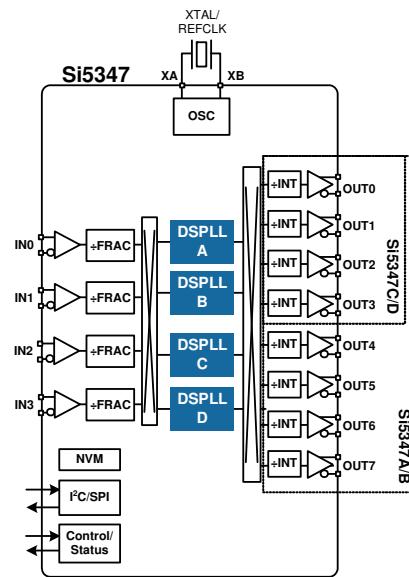


TABLE OF CONTENTS

1. Typical Application Schematic	3
2. Electrical Specifications	4
3. Typical Operating Characteristics (Jitter and Phase Noise)	22
4. Detailed Block Diagram	24
5. Functional Description	26
5.1. Frequency Configuration	26
5.2. DSPLL Loop Bandwidth	26
5.3. Modes of Operation	26
5.4. Digitally-Controlled Oscillator (DCO) Mode	28
5.5. External Reference (XA/XB)	29
5.6. Inputs (IN0, IN1, IN2, IN3)	30
5.7. Fault Monitoring	33
5.8. Outputs	37
5.9. Power Management	41
5.10. In-Circuit Programming	41
5.11. Serial Interface	41
5.12. Custom Factory Preprogrammed Parts	41
5.13. How to Enable Features and/or Configuration Settings Not Available in ClockBuilder Pro for Factory Pre-programmed Devices	42
6. Register Map	44
7. Pin Descriptions	45
8. Ordering Guide	52
8.1. Ordering Part Number Fields	52
9. Package Outlines	53
9.1. Si5347 9x9 mm 64-QFN Package Diagram	53
9.2. Si5346 7x7 mm 44-QFN Package Diagram	54
10. PCB Land Pattern	55
11. Top Marking	56
12. Device Errata	57
Document Change List	58
Contact Information	59

1. Typical Application Schematic

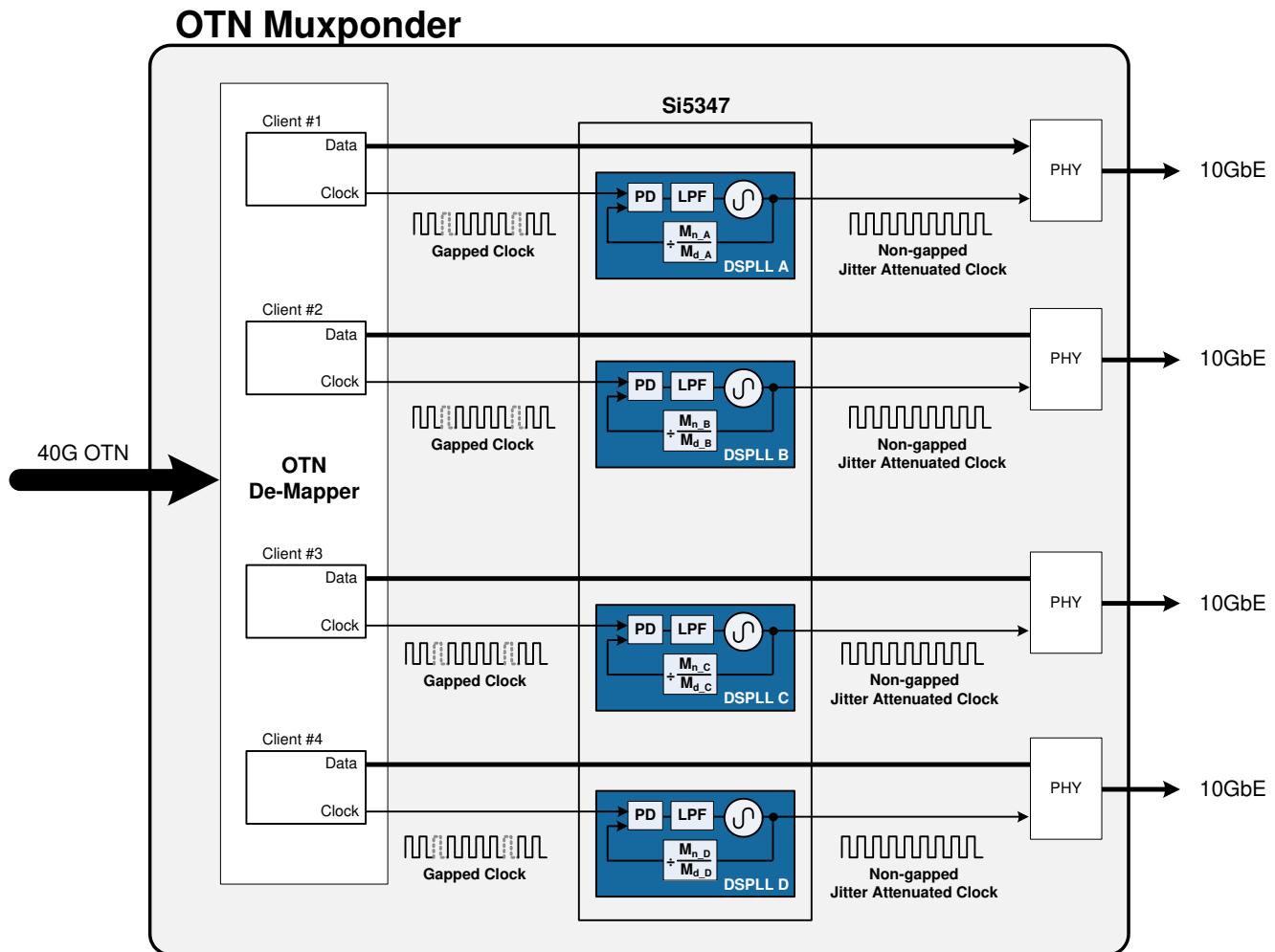


Figure 1. Using the Si5347 to Clean Gapped Clocks in an OTN Application

2. Electrical Specifications

Table 1. Recommended Operating Conditions

($V_{DD} = 1.8 \text{ V} \pm 5\%$, $V_{DDA} = 3.3 \text{ V} \pm 5\%$, $T_A = -40 \text{ to } 85 \text{ }^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit
Ambient Temperature	T_A	-40	25	85	$^\circ\text{C}$
Junction Temperature	$T_{J\text{MAX}}$	—	—	125	$^\circ\text{C}$
Core Supply Voltage	V_{DD}	1.71	1.80	1.89	V
	V_{DDA}	3.14	3.30	3.47	V
Output Driver Supply Voltage	V_{DDO}	3.14	3.30	3.47	V
		2.38	2.50	2.62	V
		1.71	1.80	1.89	V
Status Pin Supply Voltage	V_{DDS}	3.14	3.30	3.47	V
		1.71	1.80	1.89	V

Note: All minimum and maximum specifications are guaranteed and apply across the recommended operating conditions. Typical values apply at nominal supply voltages and an operating temperature of 25 °C unless otherwise noted.

Table 2. DC Characteristics

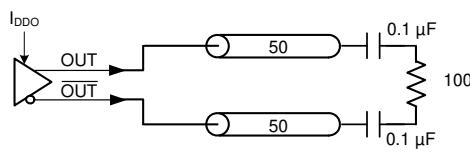
($V_{DD} = 1.8 \text{ V} \pm 5\%$, $V_{DDA} = 3.3 \text{ V} \pm 5\%$, $V_{DDO} = 1.8 \text{ V} \pm 5\%$, 2.5 V ±5%, or 3.3 V ±5%, $T_A = -40 \text{ to } 85 \text{ }^\circ\text{C}$)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Core Supply Current	I_{DD}	Si5347	Notes ^{1, 2}	—	175	240	mA
		Si5346		—	170	230	mA
	I_{DDA}	Si5347		—	120	130	mA
		Si5346		—	120	130	mA

Notes:

1. Si5347 test configuration: 7 x 2.5 V LVDS outputs enabled @156.25 MHz. Excludes power in termination resistors.
2. Si5346 test configuration: 4 x 2.5 V LVDS outputs enabled @ 156.25 MHz. Excludes power in termination resistors.
3. Differential outputs terminated into an AC coupled 100 Ω load.
4. LVC MOS outputs measured into a 5-inch 50 Ω PCB trace with 5 pF load. The LVC MOS outputs were set to OUTx_CMOS_DRV = 3, which is the strongest driver setting. Refer to the [Si5347/46 Family Reference Manual](#) for more details on register settings.
5. Detailed power consumption for any configuration can be estimated using [ClockBuilder Pro](#) when an evaluation board (EVB) is not available. All EVBs support detailed current measurements for any configuration.

Differential Output Test Configuration



LVC MOS Output Test Configuration

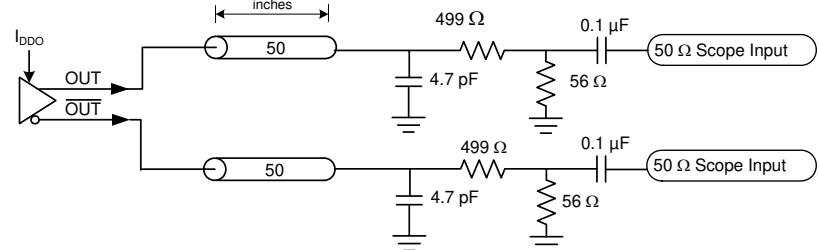


Table 2. DC Characteristics (Continued)(V_{DD} = 1.8 V ±5%, V_{DDA} = 3.3 V ±5%, V_{DDO} = 1.8 V ±5%, 2.5 V ±5%, or 3.3 V ±5%, T_A = –40 to 85 °C)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Output Buffer Supply Current	I _{DDO}	LVPECL Output ³ @ 156.25 MHz	—	21	25	mA	
		LVDS Output ³ @ 156.25 MHz	—	15	18	mA	
		3.3V LVCMOS ⁴ output @ 156.25 MHz	—	21	25	mA	
		2.5V LVCMOS ⁴ output @ 156.25 MHz	—	16	18	mA	
		1.8V LVCMOS ⁴ output @ 156.25 MHz	—	12	13	mA	
Total Power Dissipation	P _d	Si5347	Note ^{1,5}	—	980	1160	mW
		Si5346	Note ^{2,5}	—	840	1000	mW

Notes:

1. Si5347 test configuration: 7 x 2.5 V LVDS outputs enabled @156.25 MHz. Excludes power in termination resistors.
2. Si5346 test configuration: 4 x 2.5 V LVDS outputs enabled @ 156.25 MHz. Excludes power in termination resistors.
3. Differential outputs terminated into an AC coupled 100 Ω load.
4. LVCMOS outputs measured into a 5-inch 50 Ω PCB trace with 5 pF load. The LVCMOS outputs were set to OUTx_CMOS_DRV = 3, which is the strongest driver setting. Refer to the [Si5347/46 Family Reference Manual](#) for more details on register settings.
5. Detailed power consumption for any configuration can be estimated using [ClockBuilder Pro](#) when an evaluation board (EVB) is not available. All EVBs support detailed current measurements for any configuration.

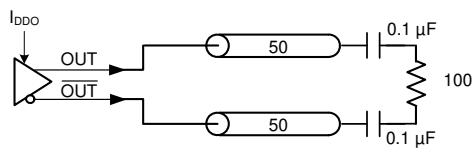
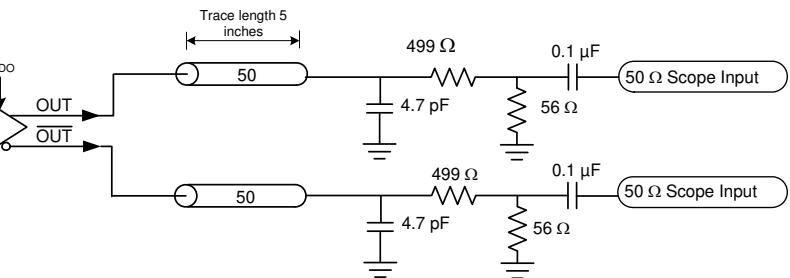
Differential Output Test Configuration**LVCMOS Output Test Configuration**

Table 3. Input Specifications

($V_{DD} = 1.8 \text{ V} \pm 5\%$, $V_{DDA} = 3.3 \text{ V} \pm 5\%$, $T_A = -40 \text{ to } 85^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Standard Differential or Single-Ended/LVC MOS — AC-coupled (IN0, IN1, IN2, IN3/FB_IN)						
Input Frequency Range	f_{IN_DIFF}	Differential	0.008	—	750	MHz
		Single-ended/LVC MOS	0.008	—	250	
Input Voltage Swing	V_{IN_DIFF}	$f_{IN} < 250 \text{ MHz}$, Differential	100	—	1800	mV_{pp_se}
		$250 \text{ MHz} < f_{IN} < 750 \text{ MHz}$, Differential	225	—	1800	mV_{pp_se}
Input Voltage Amplitude	V_{IN_SE}	$f_{IN} < 250 \text{ MHz}$, Single-ended	100	—	3600	mV_{pp_se}
Slew Rate ^{1,2}	SR		400	—	—	$\text{V}/\mu\text{s}$
Duty Cycle	DC		40	—	60	%
Capacitance	C_{IN}		—	2	—	pF
Pulsed CMOS — DC-coupled (IN0, IN1, IN2, IN3)³						
Input Frequency	f_{IN_PULSED}		0.008	—	250	MHz
Input Voltage	V_{IL}		-0.2	—	0.33	V
	V_{IH}		0.49	—	—	V
Slew Rate ^{1,2}	SR		400	—	—	$\text{V}/\mu\text{s}$
Minimum Pulse Width	PW	Pulse Input	1.6	—	—	ns
Input Resistance	R_{IN}		—	8	—	kΩ
REFCLK (Applied to XA/XB)						
REFCLK Frequency	f_{IN_REF}	Frequency range for best output jitter performance	48	—	54	MHz
Input Voltage Swing	V_{IN_DIFF}		365	—	2500	mV_{pp_diff}
	V_{IN_SE}		365	—	2000	mV_{pp_se}
Slew rate ^{1,2}	SR	Imposed for best jitter performance	400	—	—	$\text{V}/\mu\text{s}$
Input Duty Cycle	DC		40	—	60	%
Notes:						
<ol style="list-style-type: none"> 1. Imposed for jitter performance. 2. Rise and fall times can be estimated using the following simplified equation: $\text{tr}/\text{tf}_{80-20} = ((0.8 - 0.2) \times V_{IN_Vpp_se}) / SR$. 3. Pulsed CMOS mode is intended primarily for single-ended LVC MOS input clocks $\leq 1 \text{ MHz}$, which must be dc-coupled because they have a duty cycle significantly less than 50%. A typical application example is a low frequency video frame sync pulse. Since the input thresholds (V_{IL}, V_{IH}) of this buffer are non-standard (0.33 and 0.49 V, respectively), refer to the input attenuator circuit for DC-coupled Pulsed LVC MOS in the Si5347-46 Family Reference Manual. Otherwise, for standard LVC MOS input clocks, use the Standard AC-coupled, Single-ended input mode. 						

Table 4. Serial and Control Input Pin Specifications(V_{DD} = 1.8 V ±5%, V_{DDA} = 3.3 V ±5%, V_{DDS} = 3.3 V ±5%, 1.8 V ±5%, T_A = -40 to 85 °C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Si5347 Serial and Control Input Pins (I2C_SEL, RST, OE0, A1/SDO, SCLK, A0/CS, FINC, A0/CS, SDA/SDIO, DSPLL_SEL[1:0])						
Input Voltage	V _{IL}		—	—	0.3 x V _{DDIO} ¹	V
	V _{IH}		0.7 x V _{DDIO} ¹	—	—	V
Input Capacitance	C _{IN}		—	2	—	pF
Input Resistance	R _L		—	20	—	kΩ
Minimum Pulse Width	PW	RST, FINC	100	—	—	ns
Update Rate	F _{UR}	FINC	—	—	1	MHz
Si5347 Control Input Pins (FDEC, OE1)						
Input Voltage	V _{IL}		—	—	0.3 x V _{DDS}	V
	V _{IH}		0.7 x V _{DDS}	—	—	V
Input Capacitance	C _{IN}		—	2	—	pF
Minimum Pulse Width	PW	FDEC	100	—	—	ns
Update Rate	F _{UR}	FDEC	—	—	1	MHz
Si5346 Serial and Control Input Pins (I2C_SEL, RST, OE0, OE1, A1/SDO, SCLK, A0/CS, SDA/SDIO)						
Input Voltage	V _{IL}		—	—	0.3 x V _{DDIO} ¹	V
	V _{IH}		0.7 x V _{DDIO} ¹	—	—	V
Input Capacitance	C _{IN}		—	2	—	pF
Input Resistance	R _L		—	20	—	kΩ
Minimum Pulse Width	PW	RST	100	—	—	ns
Note:						
1. V _{DDIO} is determined by the IO_VDD_SEL bit. It is selectable as V _{DDA} or V _{DD} .						

Table 5. Differential Clock Output Specifications

($V_{DD} = 1.8 \text{ V} \pm 5\%$, $V_{DDA} = 3.3 \text{ V} \pm 5\%$, $V_{DDO} = 1.8 \text{ V} \pm 5\%$, $2.5 \text{ V} \pm 5\%$, or $3.3 \text{ V} \pm 5\%$, $T_A = -40 \text{ to } 85^\circ\text{C}$)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Output Frequency	f_{OUT}			0.0001	—	712.5	MHz
Duty Cycle	DC	$f_{OUT} < 400 \text{ MHz}$		48	—	52	%
		$400 \text{ MHz} < f_{OUT} < 712.5 \text{ MHz}$		44	—	55	%
Output-Output Skew	T_{SK}	Differential Output, Normal Swing Mode		—	20	50	ps
		Differential Output, Low Power Swing Mode		—	20	100	ps
OUT-OUT Skew	T_{SK_OUT}	Measured from the positive to negative output pins		—	0	100	ps
Output Voltage Amplitude ¹	Normal Mode						
	V_{OUT}	$V_{DDO} = 3.3 \text{ V},$ $2.5 \text{ V}, \text{ or } 1.8 \text{ V}$	LVDS	350	470	550	mVpp_se
		$V_{DDO} = 3.3 \text{ V},$ 2.5 V	LVPECL	660	810	1000	
	Low Power Mode						
	V_{OUT}	$V_{DDO} = 3.3 \text{ V},$ $2.5 \text{ V}, \text{ or } 1.8 \text{ V}$	LVDS	300	420	530	mVpp_se
		$V_{DDO} = 3.3 \text{ V},$ 2.5 V	LVPECL	620	820	1060	

Notes:

1. Output amplitude and common mode voltage are programmable through register settings and can be stored in NVM. Each output driver can be programmed independently. The typical normal mode (or low power mode) LVDS maximum is 100 mV (or 80 mV) higher than the TIA/EIA-644 maximum. Refer to the [Si5347/46 Family Reference Manual](#) for more suggested output settings. Not all combinations of voltage amplitude and common mode voltages settings are possible.
2. Driver output impedance depends on selected output mode (Normal, Low Power). Refer to the [Si5347/46 Family Reference Manual](#) for more information.
3. Measured for 156.25 MHz carrier frequency. Sinewave noise added to VDDO ($1.8 \text{ V} = 50 \text{ mVpp}$, $2.5 \text{ V}/$
 $3.3 \text{ V} = 100 \text{ mVpp}$) and noise spur amplitude measured.
4. Measured across two adjacent outputs, both in LVDS mode, with the victim running at 155.52 MHz and the aggressor at 156.25 MHz. Refer to application note, “[AN862: Optimizing Si534x Jitter Performance in Next Generation Internet Infrastructure Systems](#)”, guidance on crosstalk minimization. Note that all active outputs must be terminated when measuring crosstalk.

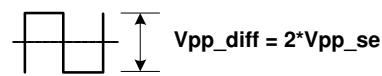
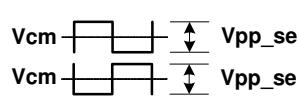
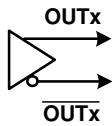


Table 5. Differential Clock Output Specifications (Continued)(V_{DD} = 1.8 V ±5%, V_{DDA} = 3.3V ±5%, V_{DDO} = 1.8 V ±5%, 2.5 V ±5%, or 3.3 V ±5%, T_A = -40 to 85 °C)

Parameter	Symbol	Test Condition			Min	Typ	Max	Unit
Common Mode Voltage ^{1,2,3}	V _{CM}	Normal Mode or Low Power Modes			1.10 1.90 1.15 0.87	1.25 2.05 1.25 0.93	1.35 2.15 1.35 1.00	V
		V _{DDO} = 3.3 V	LVDS	LVPECL				
		V _{DDO} = 2.5 V	LVPECL, LVDS					
		V _{DDO} = 1.8 V	sub-LVDS					
Rise and Fall Times (20% to 80%)	t _R /t _F	Normal Mode			—	170	240	ps
		Low Power Mode			—	300	430	
Differential Output Impedance ²	Z _O	Normal Mode			—	100	—	Ω
		Low Power Mode			—	650	—	Ω

Notes:

1. Output amplitude and common mode voltage are programmable through register settings and can be stored in NVM. Each output driver can be programmed independently. The typical normal mode (or low power mode) LVDS maximum is 100 mV (or 80 mV) higher than the TIA/EIA-644 maximum. Refer to the [Si5347/46 Family Reference Manual](#) for more suggested output settings. Not all combinations of voltage amplitude and common mode voltages settings are possible.
2. Driver output impedance depends on selected output mode (Normal, Low Power). Refer to the [Si5347/46 Family Reference Manual](#) for more information.
3. Measured for 156.25 MHz carrier frequency. Sinewave noise added to VDDO (1.8 V = 50 mVpp, 2.5 V/3.3 V = 100 mVpp) and noise spur amplitude measured.
4. Measured across two adjacent outputs, both in LVDS mode, with the victim running at 155.52 MHz and the aggressor at 156.25 MHz. Refer to application note, "[AN862: Optimizing Si534x Jitter Performance in Next Generation Internet Infrastructure Systems](#)", guidance on crosstalk minimization. Note that all active outputs must be terminated when measuring crosstalk.

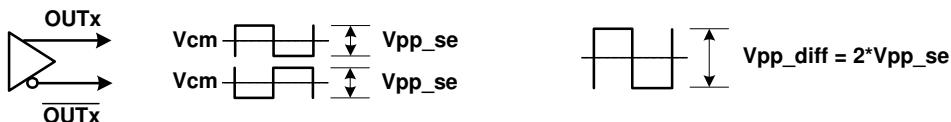


Table 5. Differential Clock Output Specifications (Continued)

($V_{DD} = 1.8 \text{ V} \pm 5\%$, $V_{DDA} = 3.3 \text{ V} \pm 5\%$, $V_{DDO} = 1.8 \text{ V} \pm 5\%$, $2.5 \text{ V} \pm 5\%$, or $3.3 \text{ V} \pm 5\%$, $T_A = -40 \text{ to } 85^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Supply Noise Rejection ³	PSRR	Normal Mode				
		10 kHz sinusoidal noise	—	-93	—	dBc
		100 kHz sinusoidal noise	—	-93	—	
		500 kHz sinusoidal noise	—	-84	—	
		1 MHz sinusoidal noise	—	-79	—	
		Low Power Mode				
		10 kHz sinusoidal noise	—	-98	—	dBc
		100 kHz sinusoidal noise	—	-95	—	
		500 kHz sinusoidal noise	—	-84	—	
		1 MHz sinusoidal noise	—	-76	—	
Output-output Crosstalk ⁴	XTALK	Si5347	—	-75	—	dB
		Si5346	—	-85	—	dB

Notes:

1. Output amplitude and common mode voltage are programmable through register settings and can be stored in NVM. Each output driver can be programmed independently. The typical normal mode (or low power mode) LVDS maximum is 100 mV (or 80 mV) higher than the TIA/EIA-644 maximum. Refer to the [Si5347/46 Family Reference Manual](#) for more suggested output settings. Not all combinations of voltage amplitude and common mode voltages settings are possible.
2. Driver output impedance depends on selected output mode (Normal, Low Power). Refer to the [Si5347/46 Family Reference Manual](#) for more information.
3. Measured for 156.25 MHz carrier frequency. Sinewave noise added to V_{DDO} ($1.8 \text{ V} = 50 \text{ mVpp}$, $2.5 \text{ V} / 3.3 \text{ V} = 100 \text{ mVpp}$) and noise spur amplitude measured.
4. Measured across two adjacent outputs, both in LVDS mode, with the victim running at 155.52 MHz and the aggressor at 156.25 MHz. Refer to application note, "[AN862: Optimizing Si534x Jitter Performance in Next Generation Internet Infrastructure Systems](#)", guidance on crosstalk minimization. Note that all active outputs must be terminated when measuring crosstalk.

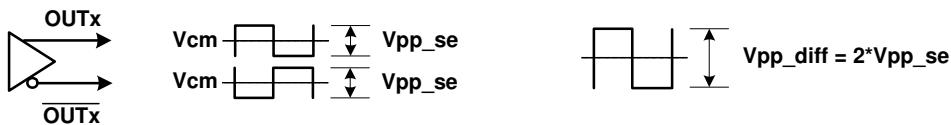


Table 6. LVC MOS Clock Output Specifications(V_{DD} = 1.8 V ±5%, V_{DDA} = 3.3 V ±5%, V_{DDO} = 1.8 V ±5%, 2.5 V ±5%, or 3.3 V ±5%, T_A = -40 to 85 °C)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Output Frequency	f _{OUT}			0.0001	—	250	MHz
Duty Cycle	DC	f _{OUT} < 100 MHz		47	—	53	%
		100 MHz < f _{OUT} < 250 MHz		44	—	55	
Output-to-Output Skew	T _{SK}	LVC MOS outputs		—	—	100	ps
Output Voltage High ^{1, 2, 3}	V _{OH}	V _{DDO} = 3.3 V					
		OUTx_CMOS_DRV=1	I _{OH} = -10 mA	V _{DDO} × 0.75	—	—	V
		OUTx_CMOS_DRV=2	I _{OH} = -12 mA		—	—	
		OUTx_CMOS_DRV=3	I _{OH} = -17 mA		—	—	
		V _{DDO} = 2.5 V					
		OUTx_CMOS_DRV=1	I _{OH} = -6 mA	V _{DDO} × 0.75	—	—	V
		OUTx_CMOS_DRV=2	I _{OH} = -8 mA		—	—	
		OUTx_CMOS_DRV=3	I _{OH} = -11 mA		—	—	
		V _{DDO} = 1.8 V					
		OUTx_CMOS_DRV=2	I _{OH} = -4 mA	V _{DDO} × 0.75	—	—	V
		OUTx_CMOS_DRV=3	I _{OH} = -5 mA		—	—	

Notes:

- Driver strength is a register programmable setting and stored in NVM. Options are OUTx_CMOS_DRV = 1, 2, 3. Refer to the [Si5347/46 Family Reference Manual](#) for more details on register settings.
- I_{OL}/I_{OH} is measured at V_{OL}/V_{OH} as shown in the dc test configuration.
- A 5 pF capacitive load is assumed. The LVC MOS outputs were set to OUTx_CMOS_DRV = 3.

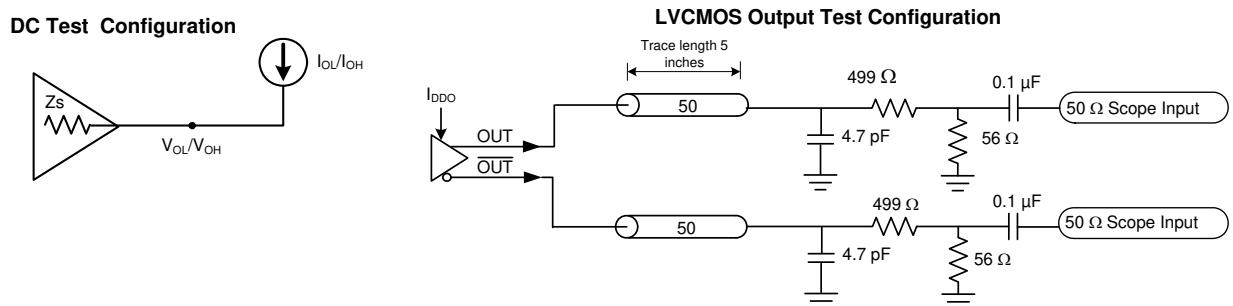


Table 6. LVC MOS Clock Output Specifications (Continued)

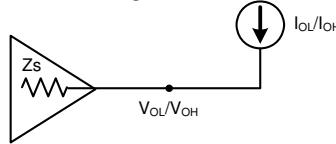
($V_{DD} = 1.8 \text{ V} \pm 5\%$, $V_{DDA} = 3.3 \text{ V} \pm 5\%$, $V_{DDO} = 1.8 \text{ V} \pm 5\%$, $2.5 \text{ V} \pm 5\%$, or $3.3 \text{ V} \pm 5\%$, $T_A = -40 \text{ to } 85^\circ\text{C}$)

Parameter	Symbol	Test Condition				Min	Typ	Max	Unit
Output Voltage Low ^{1, 2, 3}	V_{OL}	$V_{DDO} = 3.3 \text{ V}$						$V_{DDO} \times 0.15$	V
		OUTx_CMOS_DRV=1	$I_{OL} = 10 \text{ mA}$	—	—				
		OUTx_CMOS_DRV=2	$I_{OL} = 12 \text{ mA}$	—	—				
		OUTx_CMOS_DRV=3	$I_{OL} = 17 \text{ mA}$	—	—				
		$V_{DDO} = 2.5 \text{ V}$						$V_{DDO} \times 0.15$	V
		OUTx_CMOS_DRV=1	$I_{OL} = 6 \text{ mA}$	—	—				
		OUTx_CMOS_DRV=2	$I_{OL} = 8 \text{ mA}$	—	—				
		OUTx_CMOS_DRV=3	$I_{OL} = 11 \text{ mA}$	—	—				
		$V_{DDO} = 1.8 \text{ V}$						$V_{DDO} \times 0.15$	V
		OUTx_CMOS_DRV=2	$I_{OL} = 4 \text{ mA}$	—	—				
		OUTx_CMOS_DRV=3	$I_{OL} = 5 \text{ mA}$	—	—				
LVC MOS Rise and Fall Times ³ (20% to 80%)	tr/tf	$VDDO = 3.3 \text{ V}$				—	420	550	ps
		$VDDO = 2.5 \text{ V}$				—	475	625	ps
		$VDDO = 1.8 \text{ V}$				—	525	705	ps

Notes:

- Driver strength is a register programmable setting and stored in NVM. Options are OUTx_CMOS_DRV = 1, 2, 3. Refer to the [Si5347/46 Family Reference Manual](#) for more details on register settings.
- I_{OL}/I_{OH} is measured at V_{OL}/V_{OH} as shown in the dc test configuration.
- A 5 pF capacitive load is assumed. The LVC MOS outputs were set to OUTx_CMOS_DRV = 3.

DC Test Configuration



LVC MOS Output Test Configuration

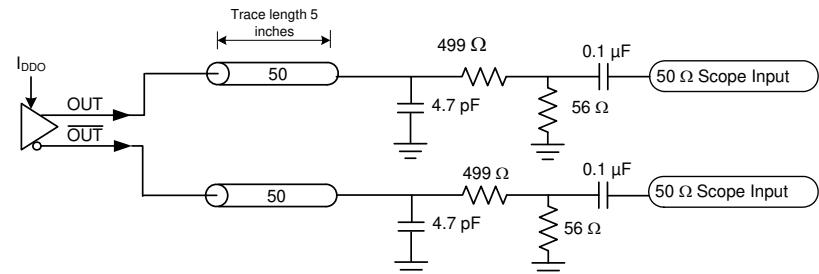


Table 7. Output Serial and Status Pin Specifications(V_{DD} = 1.8 V ±5%, V_{DDA} = 3.3 V ±5%, V_{DDS} = 3.3 V ±5%, 1.8 V ±5%, T_A = –40 to 85 °C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Si5347 Serial and Status Output Pins (LOL_A, LOL_B, LOL_C, LOL_D, INTR, LOS_XAXB, SDA/SDIO¹, A1/SDO)						
Output Voltage	V _{OH}	I _{OH} = –2 mA	V _{DDIO} ² × 0.75	—	—	V
	V _{OL}	I _{OL} = 2 mA	—	—	V _{DDIO} ² × 0.15	V
Si5346 Status Output Pins (INTR, LOS_XAXB, SDA/SDIO¹, A1/SDO)						
Output Voltage	V _{OH}	I _{OH} = –2 mA	V _{DDIO} ² × 0.75	—	—	V
	V _{OL}	I _{OL} = 2 mA	—	—	V _{DDIO} ² × 0.15	V
Si5346 Serial and Status Output Pins (LOL_A, LOL_B)						
Output Voltage	V _{OH}	I _{OH} = –2 mA	V _{DDS} × 0.75	—	—	V
	V _{OL}	I _{OL} = 2 mA	—	—	V _{DDS} × 0.15	V
Notes:						
<ol style="list-style-type: none"> 1. The V_{OH} specification does not apply to the open-drain SDA/SDIO output when the serial interface is in I²C mode or is unused with I²C_SEL pulled high. V_{OL} remains valid in all cases. 2. V_{DDIO} is determined by the IO_VDD_SEL bit. It is selectable as V_{DDA} or V_{DD}. Users normally select this option in the ClockBuilder Pro GUI. Alternatively, refer to the Si5347-46 Family Reference Manual for more details on register settings. 						

Table 8. Performance Characteristics

($V_{DD} = 1.8 \text{ V} \pm 5\%$, or $3.3 \text{ V} \pm 5\%$, $V_{DDA} = 3.3 \text{ V} \pm 5\%$, $T_A = -40 \text{ to } 85^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
PLL Loop Bandwidth Programming Range ³	f_{BW}		0.1	—	4000	Hz
Initial Start-Up Time	t_{START}	Time from power-up to when the device generates free-running clocks	—	30	45	ms
PLL Lock Time	t_{ACQ}	With Fastlock enabled, $f_{IN} = 19.44 \text{ MHz}^1$	—	500	600	ms
POR to Serial Interface Ready ²	t_{RDY}		—	—	15	ms
Jitter Peaking	J_{PK}	Measured with a frequency plan running a 25 MHz input, 25 MHz output, and a loop bandwidth of 4 Hz	—	—	0.1	dB
Jitter Tolerance	J_{TOL}	Compliant with G.8262 Options 1&2 Carrier Frequency = 10.3125 GHz Jitter Modulation Frequency = 10 Hz	—	3180	—	UI pk-pk
Maximum Phase Transient During a Hitless Switch	t_{SWITCH}	Only valid for a single switch between two input clocks running at the same frequency	—	—	2.8	ns
Pull-in Range	ω_P		—	500	—	ppm
Input-to-Output Delay Variation	$t_{IODELAY}$		—	2	—	ns
RMS Phase Jitter ⁴	J_{GEN}	12 kHz to 20 MHz	—	0.090	0.165	ps RMS

Notes:

1. Lock Time can vary significantly depending on several parameters, such as bandwidths, LOL thresholds, etc. For this case, lock time was measured with nominal and fastlock bandwidths, both set to 100 Hz, LOL set/clear thresholds of 3/0.3 ppm respectively, using IN0 as clock reference by removing the reference and enabling it again, then measuring the delta time between the first rising edge of the clock reference and the LOL indicator de-assertion.
2. Measured as time from valid VDD/VDDA rails (90% of their value) to when the serial interface is ready to respond to commands.
3. Actual loop bandwidth might be lower; please refer to CBPro for actual value on your frequency plan.
4. Jitter generation test conditions: $f_{IN} = 19.44 \text{ MHz}$, $f_{OUT} = 156.25 \text{ MHz}$ LVPECL, loop bandwidth = 100 Hz.
Does not include jitter from input reference.

Table 9. I²C Timing Specifications (SCL,SDA)

Parameter	Symbol	Test Condition	Standard Mode 100 kbps		Fast Mode 400 kbps		Unit
			Min	Max	Min	Max	
SCL Clock Frequency	f _{SCL}		—	100	—	400	kHz
SMBus Timeout	—	When Timeout is Enabled	25	35	25	35	ms
Hold Time (repeated) START Condition	t _{HD:STA}		4.0	—	0.6	—	μs
Low Period of the SCL Clock	t _{LOW}		4.7	—	1.3	—	μs
HIGH Period of the SCL Clock	t _{HIGH}		4.0	—	0.6	—	μs
Set-up Time for a Repeated START Condition	t _{SU:STA}		4.7	—	0.6	—	μs
Data Hold Time	t _{HD:DAT}		100	—	100	—	ns
Data Set-up Time	t _{SU:DAT}		250	—	100	—	ns
Rise Time of Both SDA and SCL Signals	t _r		—	1000	20	300	ns
Fall Time of Both SDA and SCL Signals	t _f		—	300	—	300	ns
Set-up Time for STOP Condition	t _{SU:STO}		4.0	—	0.6	—	μs
Bus Free Time between a STOP and START Condition	t _{BUF}		4.7	—	1.3	—	μs
Data Valid Time	t _{VD:DAT}		—	3.45	—	0.9	μs
Data Valid Acknowledge Time	t _{VD:ACK}		—	3.45	—	0.9	μs

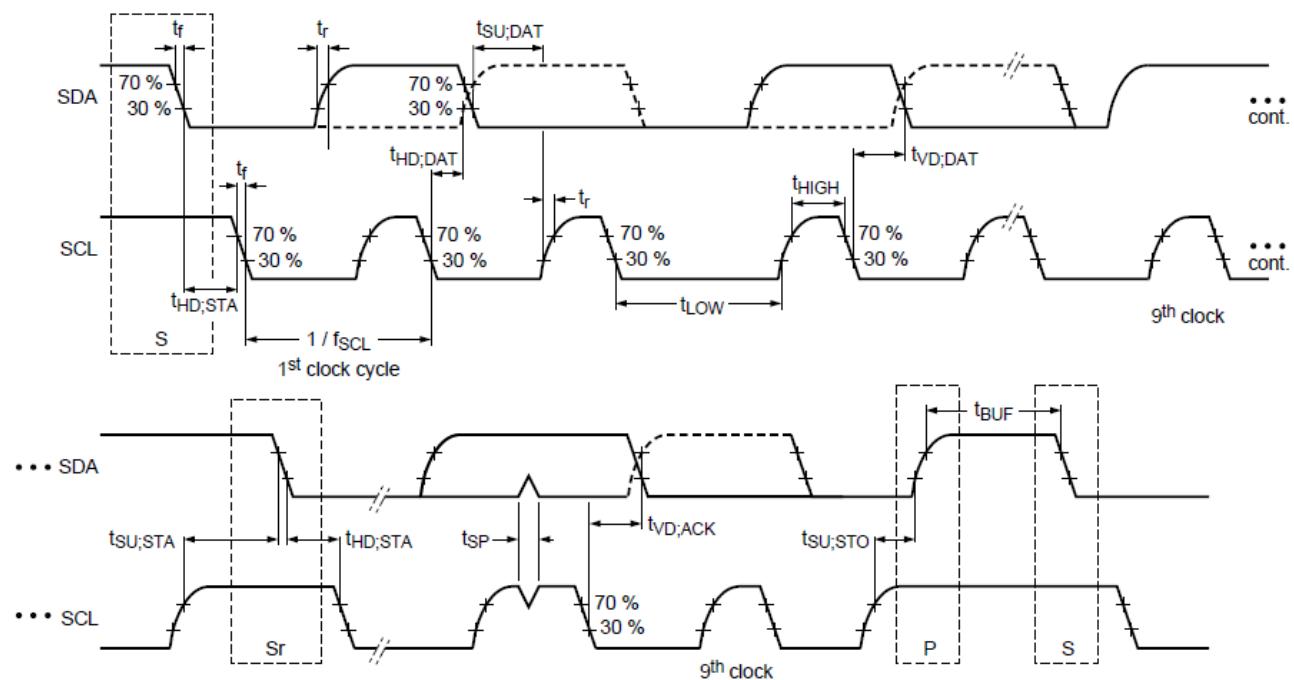


Figure 2. I²C Serial Port Timing Standard and Fast Modes

Table 10. SPI Timing Specifications (4-Wire)(V_{DD} = 1.8 V ±5%, V_{DDA} = 3.3 V ±5%, T_A = -40 to 85 °C)

Parameter	Symbol	Min	Typ	Max	Unit
SCLK Frequency	f _{SPI}	—	—	20	MHz
SCLK Duty Cycle	T _{DC}	40	—	60	%
SCLK Period	T _C	50	—	—	ns
Delay Time, SCLK Fall to SDO Active	T _{D1}	—	—	18	ns
Delay Time, SCLK Fall to SDO	T _{D2}	—	—	15	ns
Delay Time, CS Rise to SDO Tri-State	T _{D3}	—	—	15	ns
Setup Time, CS to SCLK	T _{SU1}	5	—	—	ns
Hold Time, SCLK Fall to CS	T _{H1}	5	—	—	ns
Setup Time, SDI to SCLK Rise	T _{SU2}	5	—	—	ns
Hold Time, SDI to SCLK Rise	T _{H2}	5	—	—	ns
Delay Time Between Chip Selects (CS)	T _{CS}	2	—	—	T _C

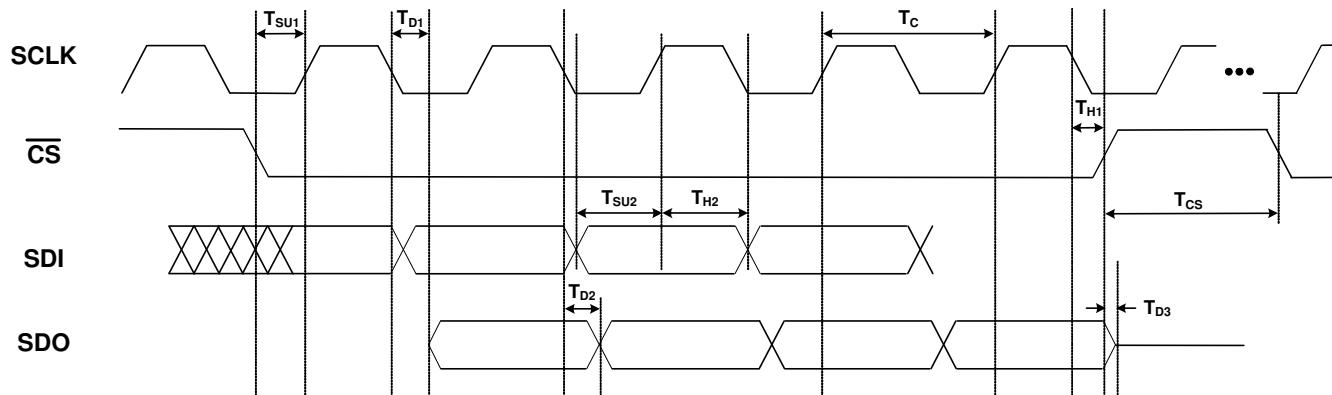
**Figure 3. 4-Wire SPI Serial Interface Timing**

Table 11. SPI Timing Specifications (3-Wire)

($V_{DD} = 1.8 \text{ V} \pm 5\%$, $V_{DDA} = 3.3 \text{ V} \pm 5\%$, $T_A = -40 \text{ to } 85^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Units
SCLK Frequency	f_{SPI}	—	—	20	MHz
SCLK Duty Cycle	T_{DC}	40	—	60	%
SCLK Period	T_C	50	—	—	ns
Delay Time, SCLK Fall to SDIO Turn-on	T_{D1}	—	—	20	ns
Delay Time, SCLK Fall to SDIO Next-bit	T_{D2}	—	—	15	ns
Delay Time, $\overline{\text{CS}}$ Rise to SDIO Tri-State	T_{D3}	—	—	15	ns
Setup Time, $\overline{\text{CS}}$ to SCLK	T_{SU1}	5	—	—	ns
Hold Time, SCLK Fall to $\overline{\text{CS}}$	T_{H1}	5	—	—	ns
Setup Time, SDI to SCLK Rise	T_{SU2}	5	—	—	ns
Hold Time, SDI to SCLK Rise	T_{H2}	5	—	—	ns
Delay Time Between Chip Selects ($\overline{\text{CS}}$)	T_{CS}	2	—	—	T_C

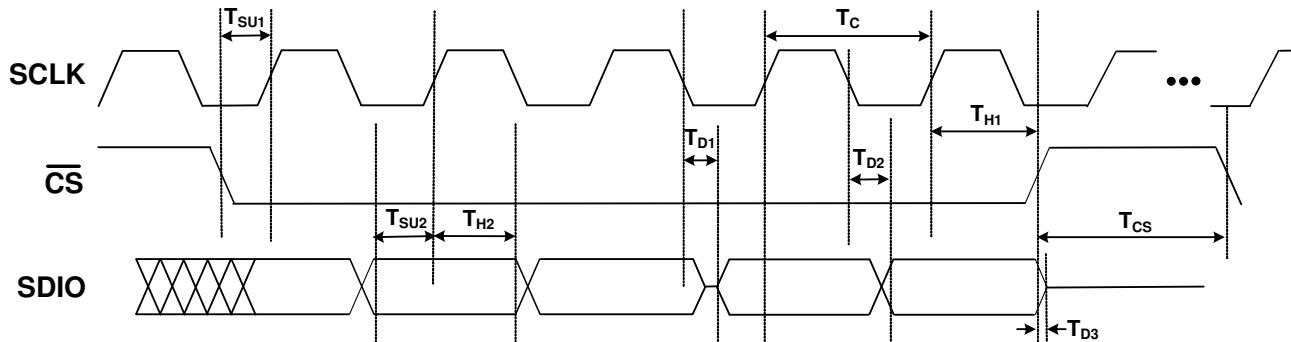


Figure 4. 3-Wire SPI Serial Interface Timing

Table 12. Crystal Specifications

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal Frequency Range	f_{XTAL_48-54}	Frequency range for best jitter performance	48	—	54	MHz
Load Capacitance	C_L_{48-54}		—	8	—	pF
Shunt Capacitance	C_O_{48-54}		—	—	2	pF
Crystal Drive Level	d_L_{48-54}		—	—	200	μW
Equivalent Series Resistance	r_{ESR_48-54}	Refer to the Si5347/46 Family Reference Manual to determine ESR.				
Crystal Frequency Range	f_{XTAL_25}		—	25	—	MHz
Load Capacitance	C_L_{25}		—	8	—	pF
Shunt Capacitance	C_O_{25}		—	—	3	pF
Crystal Drive Level	d_L_{25}		—	—	200	μW
Equivalent Series Resistance	r_{ESR_25}	Refer to the Si5347/46 Family Reference Manual to determine ESR.				

Notes:

1. The Si5347/46 is designed to work with crystals that meet the frequencies and specifications in Table 12.
2. Refer to the [Si5347/46 Family Reference Manual](#) for recommended 48 to 54 MHz crystals.

Si5347/46

Table 13. Thermal Characteristics

Parameter	Symbol	Test Condition ¹	Value	Unit	
Si5347–64QFN					
Thermal Resistance Junction to Ambient	θ_{JA}	Still Air	22	°C/W	
		Air Flow 1 m/s	19.4		
		Air Flow 2 m/s	18.3		
Thermal Resistance Junction to Case	θ_{JC}		9.5		
Thermal Resistance Junction to Board	θ_{JB}		9.4	°C/W	
	ψ_{JB}		9.3		
Thermal Resistance Junction to Top Center	ψ_{JT}		0.2		
Si5346–44QFN					
Thermal Resistance Junction to Ambient	θ_{JA}	Still Air	22.3	°C/W	
		Air Flow 1 m/s	19.4		
		Air Flow 2 m/s	18.4		
Thermal Resistance Junction to Case	θ_{JC}		10.9		
Thermal Resistance Junction to Board	θ_{JB}		9.3	°C/W	
	ψ_{JB}		9.2		
Thermal Resistance Junction to Top Center	ψ_{JT}		0.23		
Notes:					
1. Based on PCB Dimension: 3" x 4.5", PCB Thickness: 1.6 mm, PCB Land/Via under GNP pad: 36, Number of Cu Layers: 4					

Table 14. Absolute Maximum Ratings^{1,2,3}

Parameter	Symbol	Test Condition	Value	Unit
DC Supply Voltage	V _{DD}		−0.5 to 3.8	V
	V _{DDA}		−0.5 to 3.8	V
	V _{DDO}		−0.5 to 3.8	V
	V _{DDS}		−0.5 to 3.8	V
Input Voltage Range	V _{I1}	IN0 – IN3/FB_IN	−0.85 to 3.8	V
	V _{I2}	RST, OE0, OE1, I ₂ C_SEL, FINC, FDEC, PLL_SEL[1:0], SDA/SDIO, A1/SDO, SCLK, A0/CS	−0.5 to 3.8	V
	V _{I3}	XA/XB	−0.5 to 2.7	V
Latch-up Tolerance	LU		JESD78 Compliant	
ESD Tolerance	HBM	100 pF, 1.5 kΩ	2.0	kV
Junction Temperature	T _{JCT}		−55 to 150	°C
Storage Temperature Range	T _{STG}		−55 to +150	°C
Soldering Temperature (Pb-free profile) ³	T _{PEAK}		260	°C
Soldering Temperature Time at T _{PEAK} (Pb-free profile) ⁴	T _P		20–40	s

Note:

- 1. Permanent device damage may occur if the absolute maximum ratings are exceeded. Functional operation should be restricted to the conditions as specified in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
- 2. 64-QFN and 44-QFN packages are RoHS-6 compliant.
- 3. For detailed MSL and packaging information, go to www.silabs.com/support/quality/pages/RoHSInformation.aspx.
- 4. The device is compliant with JEDEC J-STD-020.

3. Typical Operating Characteristics (Jitter and Phase Noise)

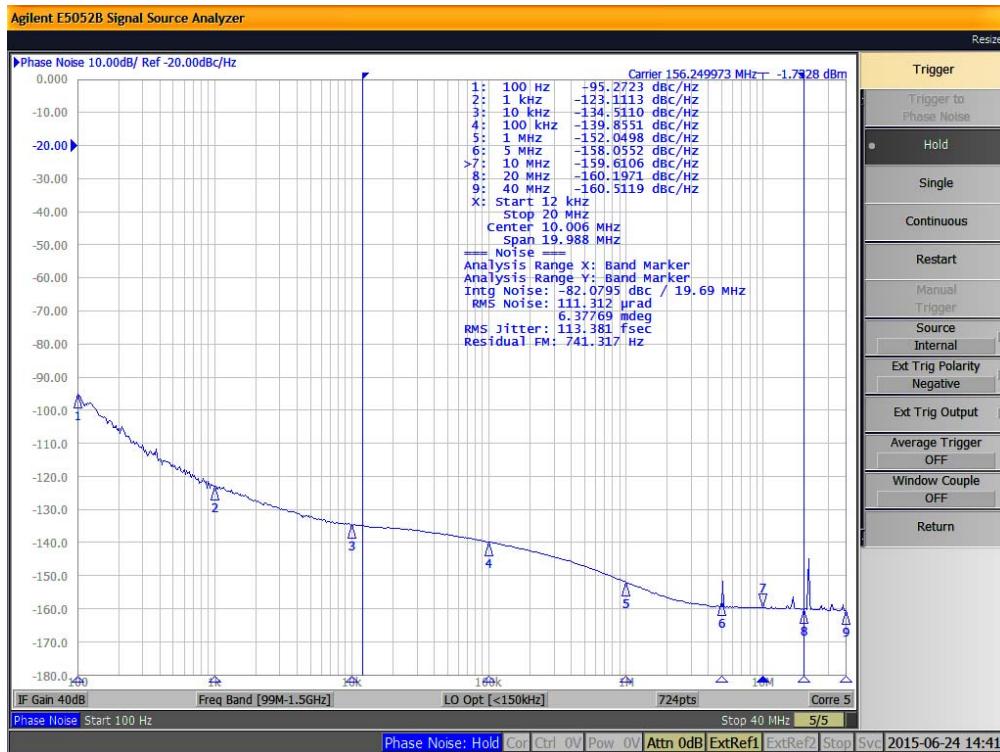


Figure 5. Input = 25 MHz; Output = 156.25 MHz, 2.5 V LVDS

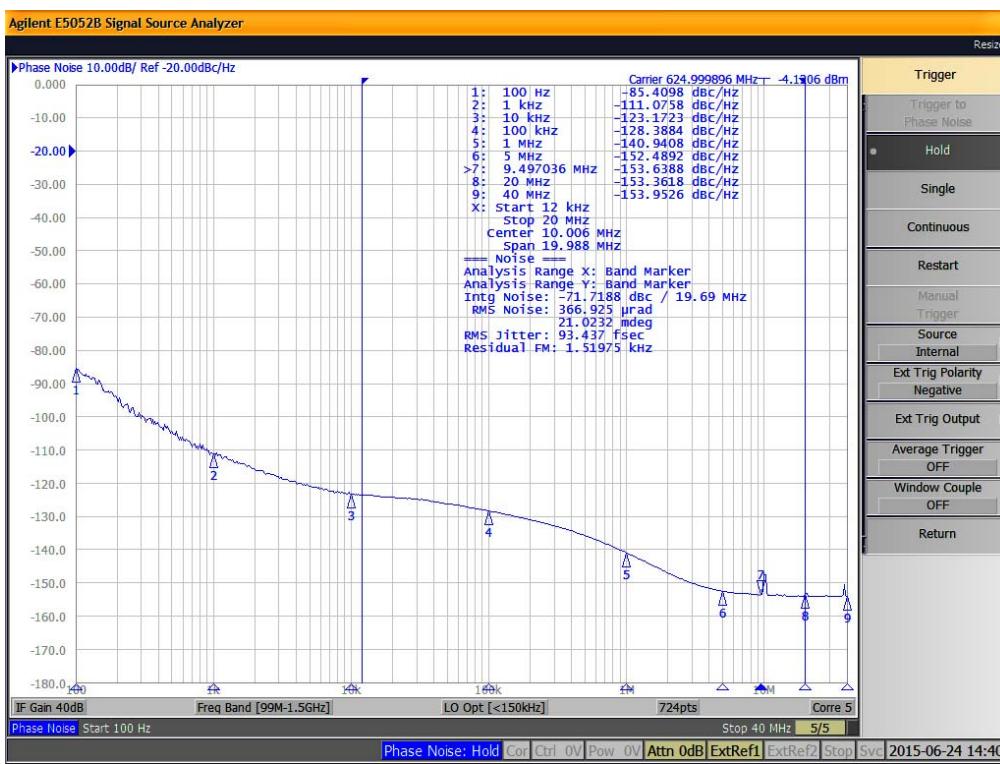


Figure 6. Input = 25 MHz; Output = 625 MHz, 2.5 V LVDS

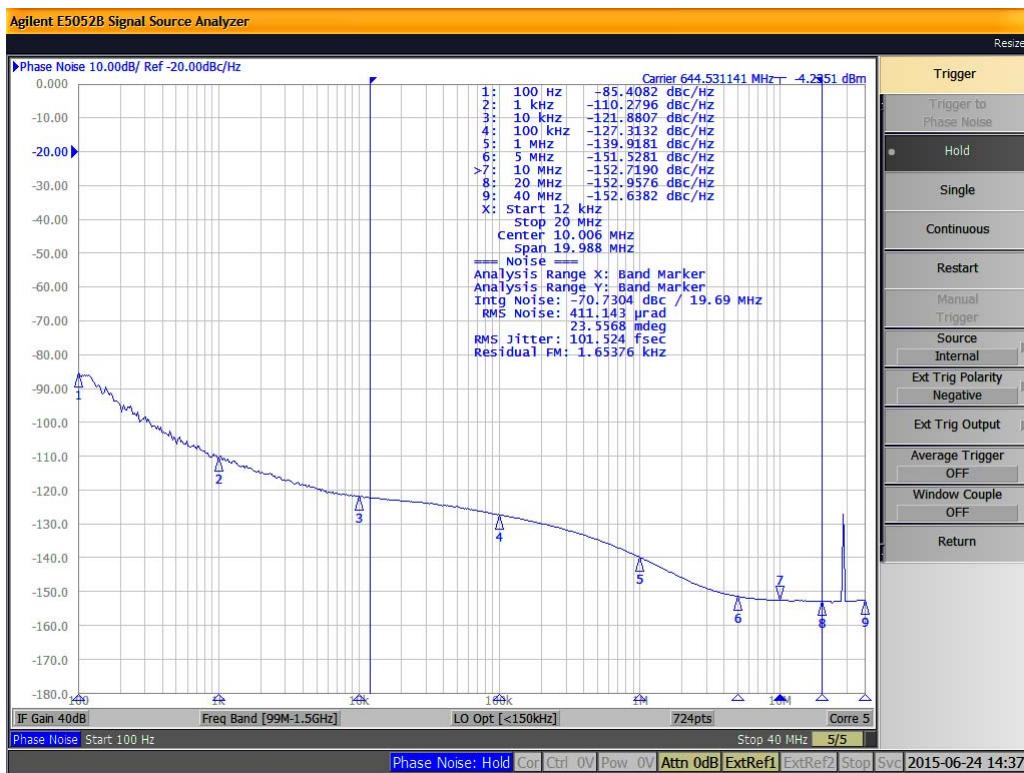


Figure 7. Input = 19.44 MHz; Output = 644.53125 MHz, 2.5 V LVDS

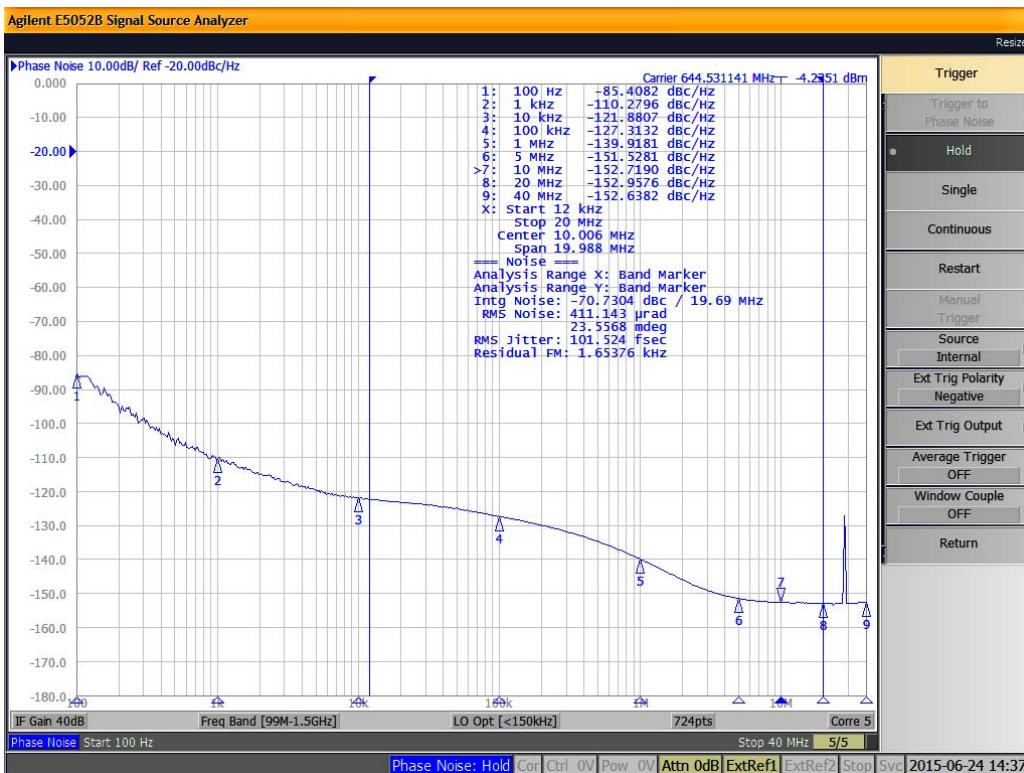


Figure 8. Input = 25 MHz; Output = 644.53125 MHz, 2.5 V LVDS

4. Detailed Block Diagram

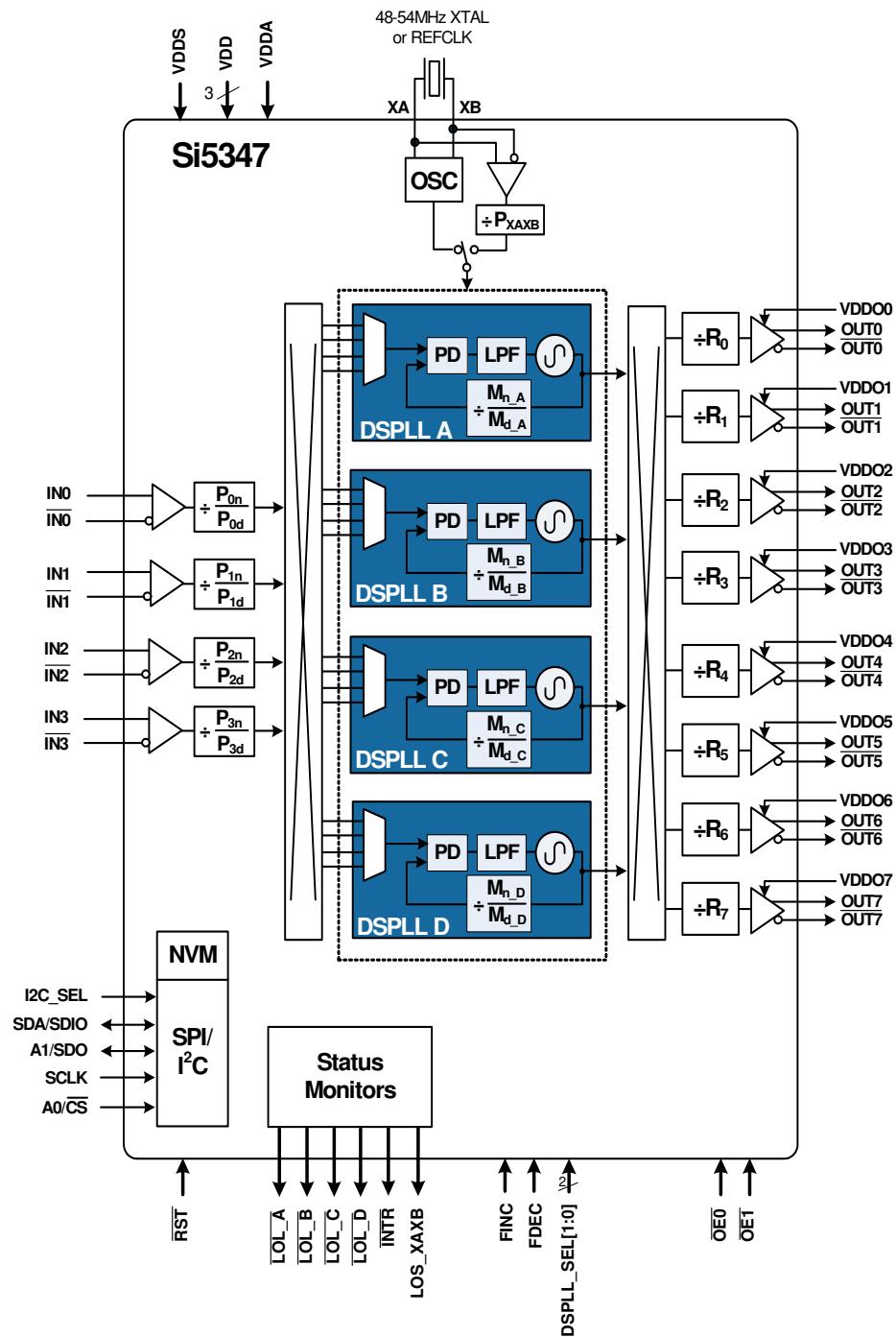


Figure 9. Si5347A/B Detailed Block Diagram

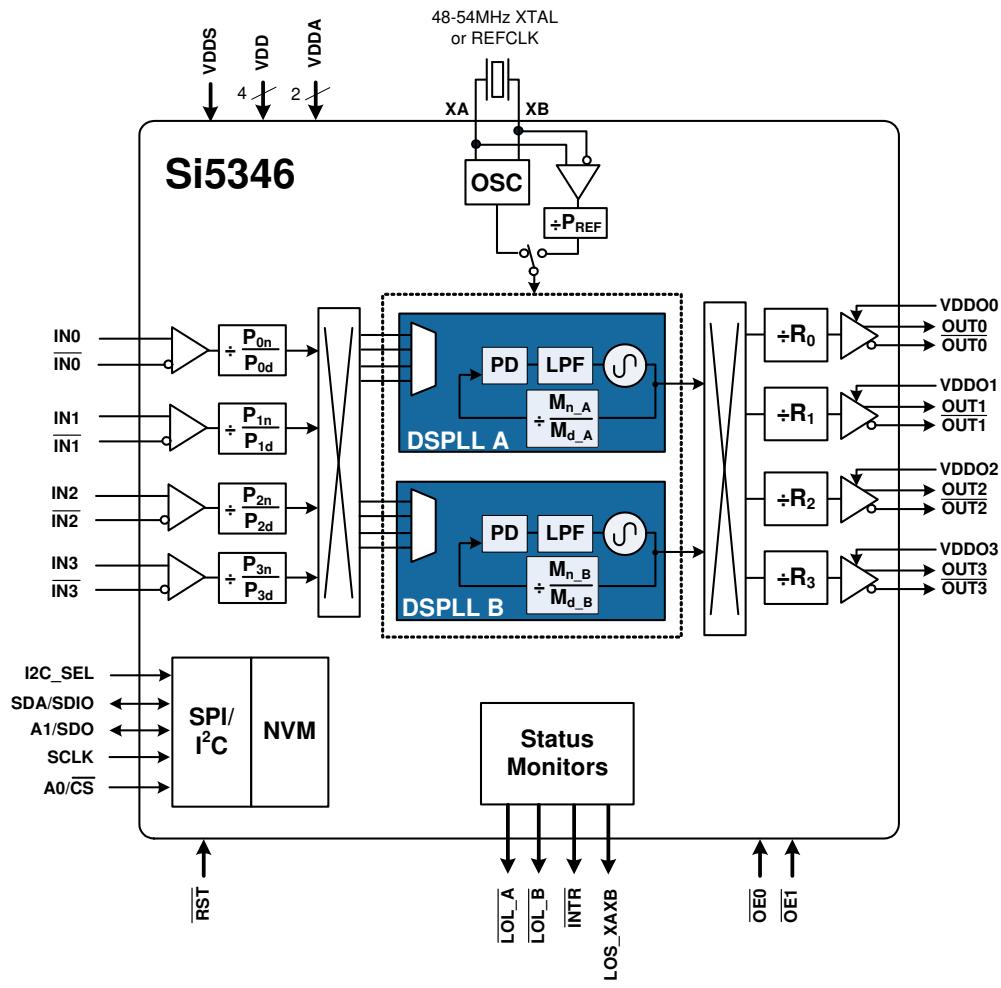


Figure 10. Si5346 Detailed Block Diagram